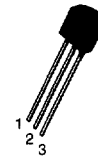
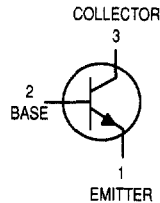


General Purpose Transistors

NPN Silicon

2N3903
2N3904*

*Motorola Preferred Device



CASE 29-04, STYLE 1
TO-92 (TO-226AA)

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector-Emitter Voltage	V_{CEO}	40	Vdc
Collector-Base Voltage	V_{CBO}	60	Vdc
Emitter-Base Voltage	V_{EBO}	6.0	Vdc
Collector Current — Continuous	I_C	200	mAdc
Total Device Dissipation @ $T_A = 25^\circ\text{C}$ Derate above 25°C	P_D	625 5.0	mW mW/ $^\circ\text{C}$
Total Device Dissipation @ $T_C = 25^\circ\text{C}$ Derate above 25°C	P_D	1.5 12	Watts mW/ $^\circ\text{C}$
Operating and Storage Junction Temperature Range	T_J, T_{stg}	-55 to +150	$^\circ\text{C}$

THERMAL CHARACTERISTICS(1)

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	200	$^\circ\text{C}/\text{W}$
Thermal Resistance, Junction to Case	$R_{\theta JC}$	83.3	$^\circ\text{C}/\text{W}$

ELECTRICAL CHARACTERISTICS ($T_A = 25^\circ\text{C}$ unless otherwise noted)

Characteristic	Symbol	Min	Max	Unit
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OFF CHARACTERISTICS

Collector-Emitter Breakdown Voltage (2) ($I_C = 1.0 \text{ mAdc}, I_B = 0$)	$V_{(BR)CEO}$	40	—	Vdc
Collector-Base Breakdown Voltage ($I_C = 10 \mu\text{Adc}, I_E = 0$)	$V_{(BR)CBO}$	60	—	Vdc
Emitter-Base Breakdown Voltage ($I_E = 10 \mu\text{Adc}, I_C = 0$)	$V_{(BR)EBO}$	6.0	—	Vdc
Base Cutoff Current ($V_{CE} = 30 \text{ Vdc}, V_{EB} = 3.0 \text{ Vdc}$)	I_{BL}	—	50	nAdc
Collector Cutoff Current ($V_{CE} = 30 \text{ Vdc}, V_{EB} = 3.0 \text{ Vdc}$)	I_{CEX}	—	50	nAdc

1. Indicates Data in addition to JEDEC Requirements.
2. Pulse Test: Pulse Width $\leq 300 \mu\text{s}$; Duty Cycle $\leq 2.0\%$.

Preferred devices are Motorola recommended choices for future use and best overall value.

REV 2

2N3903 2N3904

ELECTRICAL CHARACTERISTICS ($T_A = 25^\circ\text{C}$ unless otherwise noted) (Continued)

Characteristic	Symbol	Min	Max	Unit
ON CHARACTERISTICS				
DC Current Gain ⁽¹⁾ ($I_C = 0.1 \text{ mAdc}$, $V_{CE} = 1.0 \text{ Vdc}$)	2N3903 2N3904	20 40	— —	—
($I_C = 1.0 \text{ mAdc}$, $V_{CE} = 1.0 \text{ Vdc}$)	2N3903 2N3904	35 70	— —	—
($I_C = 10 \text{ mAdc}$, $V_{CE} = 1.0 \text{ Vdc}$)	2N3903 2N3904	50 100	150 300	—
($I_C = 50 \text{ mAdc}$, $V_{CE} = 1.0 \text{ Vdc}$)	2N3903 2N3904	30 60	— —	—
($I_C = 100 \text{ mAdc}$, $V_{CE} = 1.0 \text{ Vdc}$)	2N3903 2N3904	15 30	— —	—
Collector-Emitter Saturation Voltage ⁽¹⁾ ($I_C = 10 \text{ mAdc}$, $I_B = 1.0 \text{ mAdc}$) ($I_C = 50 \text{ mAdc}$, $I_B = 5.0 \text{ mAdc}$)	$V_{CE(sat)}$	— —	0.2 0.3	Vdc
Base-Emitter Saturation Voltage ⁽¹⁾ ($I_C = 10 \text{ mAdc}$, $I_B = 1.0 \text{ mAdc}$) ($I_C = 50 \text{ mAdc}$, $I_B = 5.0 \text{ mAdc}$)	$V_{BE(sat)}$	0.65 —	0.85 0.95	Vdc

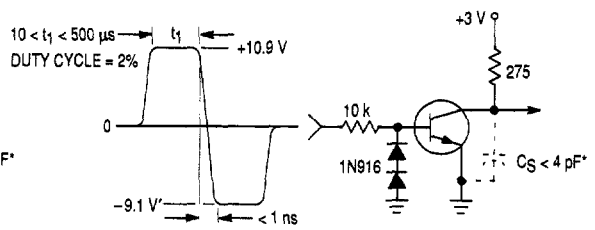
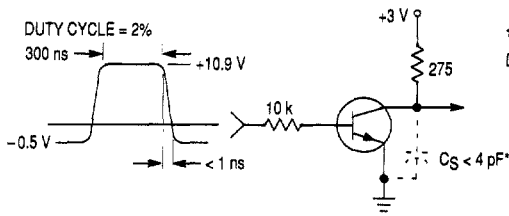
SMALL-SIGNAL CHARACTERISTICS

Current-Gain — Bandwidth Product ($I_C = 10 \text{ mAdc}$, $V_{CE} = 20 \text{ Vdc}$, $f = 100 \text{ MHz}$)	2N3903 2N3904	f_T	250 300	— —	MHz
Output Capacitance ($V_{CB} = 5.0 \text{ Vdc}$, $I_E = 0$, $f = 1.0 \text{ MHz}$)		C_{obo}	—	4.0	pF
Input Capacitance ($V_{EB} = 0.5 \text{ Vdc}$, $I_C = 0$, $f = 1.0 \text{ MHz}$)		C_{ibo}	—	8.0	pF
Input Impedance ($I_C = 1.0 \text{ mAdc}$, $V_{CE} = 10 \text{ Vdc}$, $f = 1.0 \text{ kHz}$)	2N3903 2N3904	h_{ie}	1.0 1.0	8.0 10	k Ω
Voltage Feedback Ratio ($I_C = 1.0 \text{ mAdc}$, $V_{CE} = 10 \text{ Vdc}$, $f = 1.0 \text{ kHz}$)	2N3903 2N3904	h_{re}	0.1 0.5	5.0 8.0	$\times 10^{-4}$
Small-Signal Current Gain ($I_C = 1.0 \text{ mAdc}$, $V_{CE} = 10 \text{ Vdc}$, $f = 1.0 \text{ kHz}$)	2N3903 2N3904	h_{fe}	50 100	200 400	—
Output Admittance ($I_C = 1.0 \text{ mAdc}$, $V_{CE} = 10 \text{ Vdc}$, $f = 1.0 \text{ kHz}$)		h_{oe}	1.0	40	μmhos
Noise Figure ($I_C = 100 \mu\text{Adc}$, $V_{CE} = 5.0 \text{ Vdc}$, $R_S = 1.0 \text{ k}\Omega$, $f = 1.0 \text{ kHz}$)	2N3903 2N3904	NF	— —	6.0 5.0	dB

SWITCHING CHARACTERISTICS

Delay Time	$(V_{CC} = 3.0 \text{ Vdc}$, $V_{BE} = 0.5 \text{ Vdc}$, $I_C = 10 \text{ mAdc}$, $I_{B1} = 1.0 \text{ mAdc}$)	t_d	—	35	ns
Rise Time		t_r	—	35	ns
Storage Time	$(V_{CC} = 3.0 \text{ Vdc}$, $I_C = 10 \text{ mAdc}$, $I_{B1} = I_{B2} = 1.0 \text{ mAdc}$)	t_s	—	175 200	ns
Fall Time		t_f	—	50	ns

1. Pulse Test: Pulse Width $\leq 300 \mu\text{s}$; Duty Cycle $\leq 2.0\%$.



* Total shunt capacitance of test jig and connectors

Figure 1. Delay and Rise Time Equivalent Test Circuit

Figure 2. Storage and Fall Time Equivalent Test Circuit

TYPICAL TRANSIENT CHARACTERISTICS

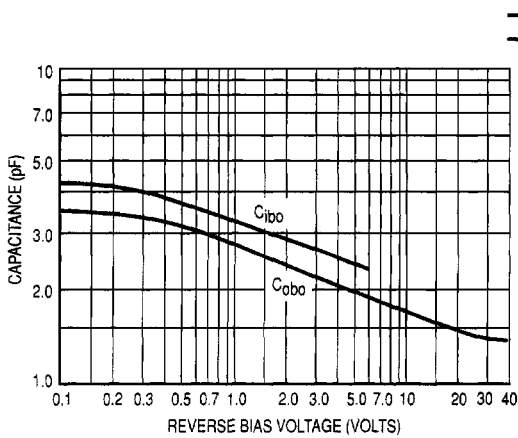


Figure 3. Capacitance

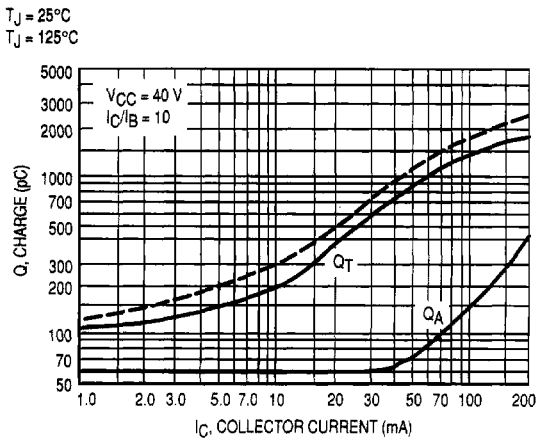


Figure 4. Charge Data

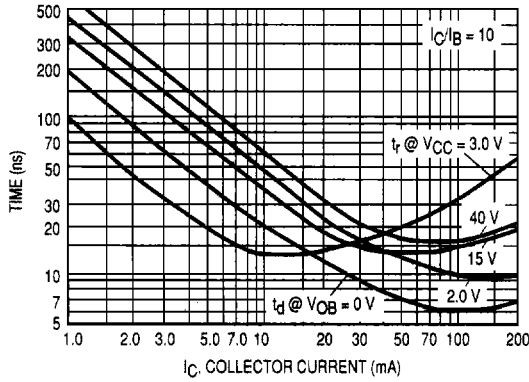


Figure 5. Turn-On Time

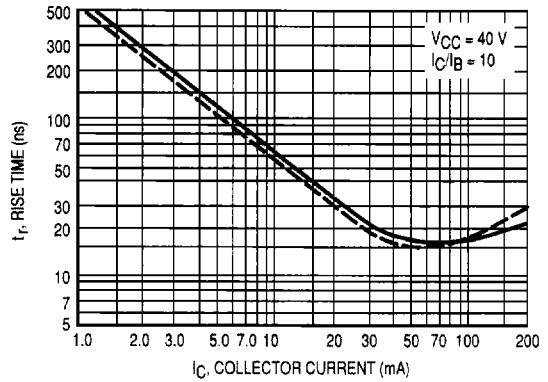


Figure 6. Rise Time

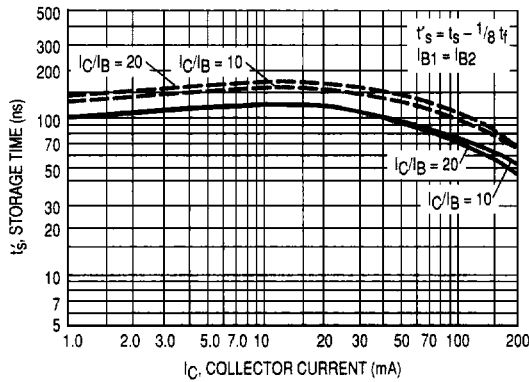


Figure 7. Storage Time

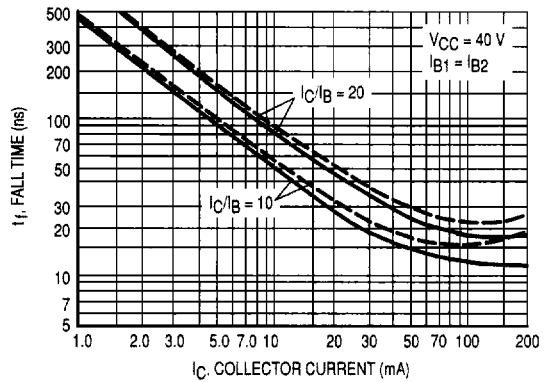


Figure 8. Fall Time

TYPICAL AUDIO SMALL-SIGNAL CHARACTERISTICS
NOISE FIGURE VARIATIONS

(V_{CE} = 5.0 Vdc, T_A = 25°C, Bandwidth = 1.0 Hz)

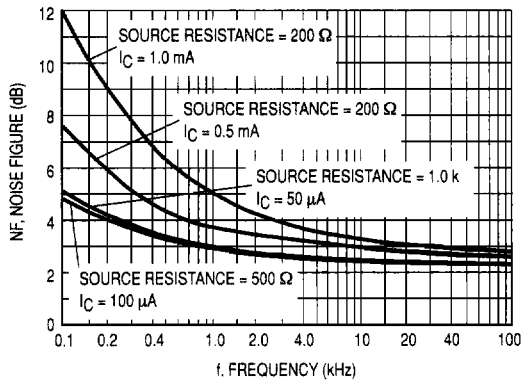


Figure 9.

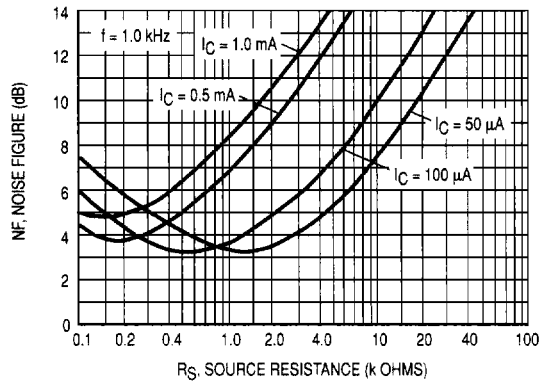


Figure 10.

h PARAMETERS

($V_{CE} = 10 \text{ Vdc}$, $f = 1.0 \text{ kHz}$, $T_A = 25^\circ\text{C}$)

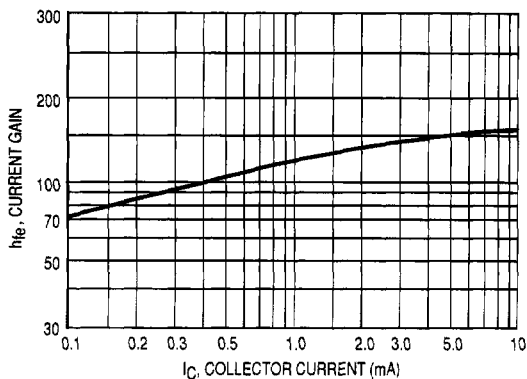


Figure 11. Current Gain

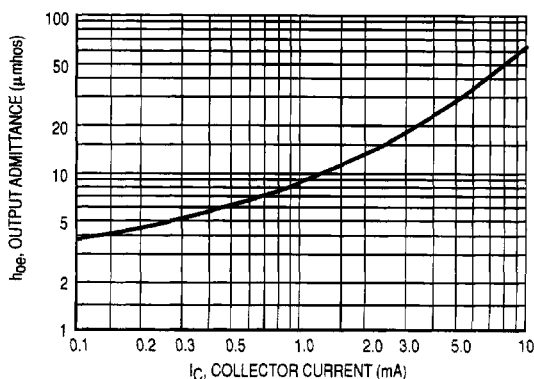


Figure 12. Output Admittance

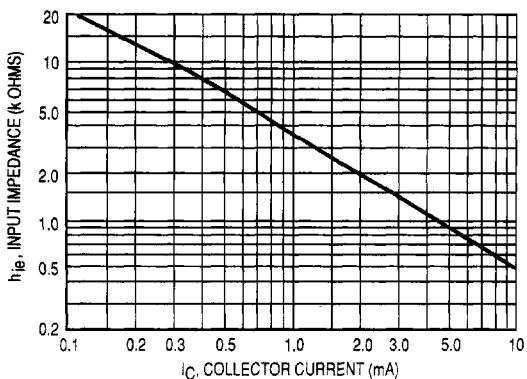


Figure 13. Input Impedance

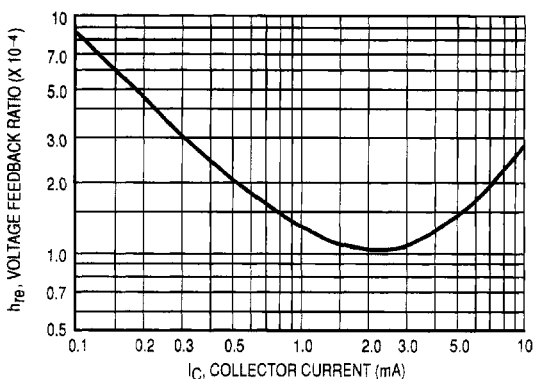


Figure 14. Voltage Feedback Ratio

TYPICAL STATIC CHARACTERISTICS

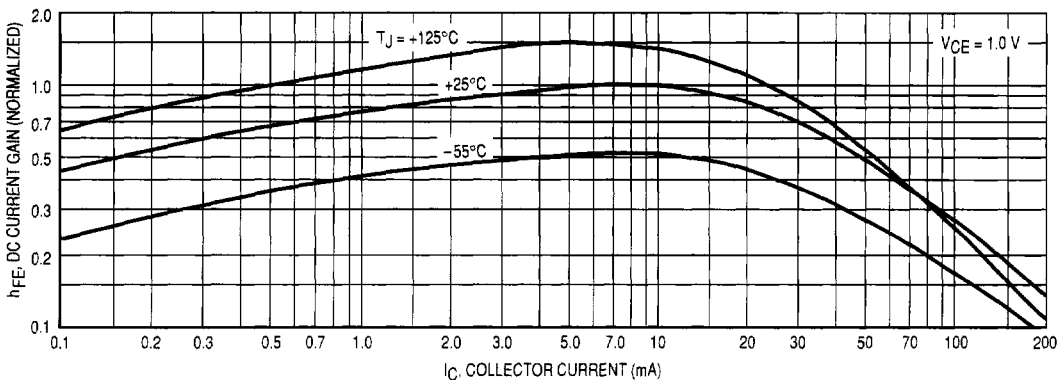


Figure 15. DC Current Gain

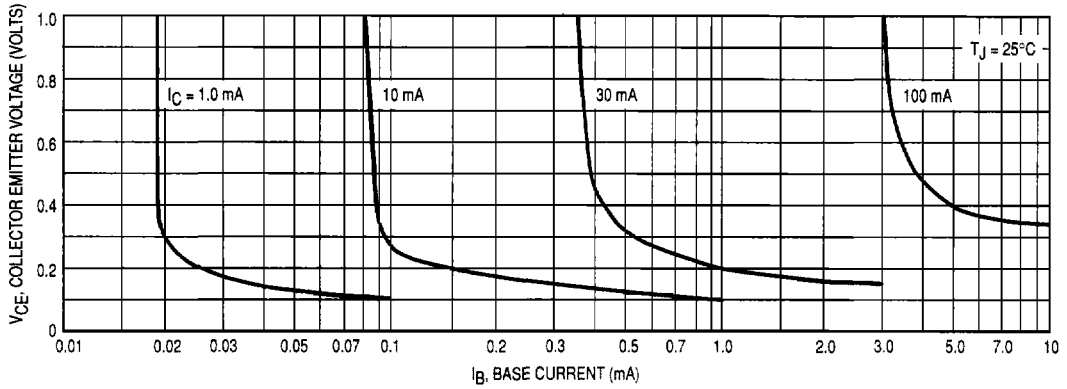


Figure 16. Collector Saturation Region

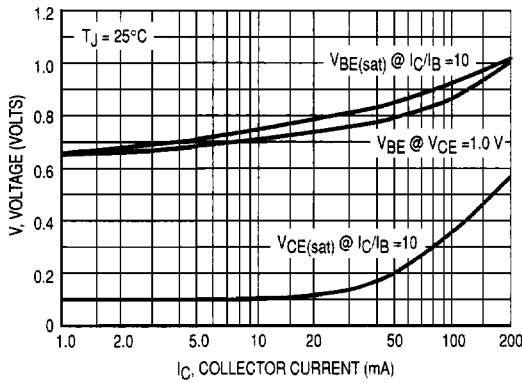


Figure 17. "ON" Voltages

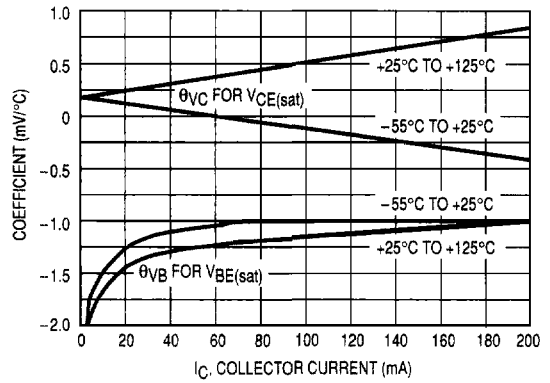


Figure 18. Temperature Coefficients